## **DESCRIPTION**

The 2SD1766 is available in SOT-89 package

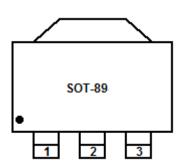
### **FEATURES**

- Low V<sub>CE(sat)</sub>, V<sub>CE(sat)</sub> = 0.5V (typical)
  (I<sub>C</sub> = 2A, I<sub>B</sub>= 0.2A).
- Available in SOT-89 package

### ORDERING INFORMATION

Package Type	Part Number				
SOT-89	2SD1766P				
	2SD1766Q				
	2SD1766R				
Note	SPQ: 1,000pcs/Reel				
AiT provides all RoHS Compliant Products					

### PIN DESCRIPTION



- 1. BASE
- 2. COLLECTOR
- 3. EMITTER

REV1.0 - SEP 2017 RELEASED - -1

### **ABSOLUTE MAXIMUM RATINGS**

#### T<sub>A</sub>=25°C

1A-23 C	
V <sub>CBO</sub> , Collector-Base Voltage	40V
V <sub>CEO</sub> , Collector-Emitter Voltage	32V
V <sub>EBO</sub> , Emitter-Base Voltage	5V
I <sub>C</sub> , Collector Current	2A
I <sub>C</sub> (Pulse) <sup>NOTE1</sup> , Collector Current	2.5A
Pc, Collector Power Dissipation	0.5W
PcNOTE2, Collector Power Dissipation	2W
T <sub>J</sub> , Junction Temperature	150°C
T <sub>STG</sub> , Storage Temperature	-55°C ~150°C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

NOTE1: Pw=20ms.

NOTE2:40X40X 0.7mm Ceramic board.

### **ELECTRICAL CHARACTERISTICS**

#### $T_A=25$ °C

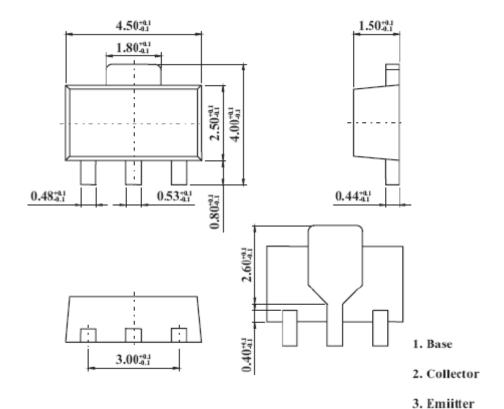
Parameter	Symbol	Conditions		Min.	Тур.	Max.	Unit
Collector-Base Voltage	ВУсво	Ic=50μA		40	ı	ı	V
Collector-Emitter Voltage	BV <sub>CEO</sub>	I <sub>C</sub> = 1mA		32	-	-	V
Emitter-Base Voltage	BV <sub>EBO</sub>	I <sub>E</sub> =50μA		5	1	1	V
Collector Cutoff Current	Ісво	V <sub>CB</sub> =20V		ı	ı	1	uA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =4V		-	1	1	uA
DC Current Gain	hFE	V <sub>CE</sub> =3V, I <sub>C</sub> =0.5A	Р	82	1	180	
			Q	120	-	270	
			R	180	-	390	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =2A, I <sub>B</sub> =0.2A		-	0.5	0.8	V
Transition Frequency	f⊤	V <sub>CE</sub> =5V, I <sub>E</sub> =-500m	ıΑ,		100	-	MHz
		f=100MHz		-			
Output Capacitance	$C_{\sf ob}$	V <sub>CB</sub> =10V, I <sub>E</sub> =0A,			30	-	pF
		f=1MHz		_			

REV1.0 - SEP 2017 RELEASED - - 2 -



# PACKAGE INFORMATION

Dimension in SOT-89 (Unit: mm)



REV1.0 - SEP 2017 RELEASED -- 3 -

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REV1.0 - SEP 2017 RELEASED - - 4 -